

L Number	Hits	Search Text	DB	Time stamp
1	14	(three adj interfaces) near5 (die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:35
2	88	(three adj interfaces) near10 (die or chip or circuit)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:44
3	19	(three adj interfaces) near10 (die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:37
4	26	(three near interfaces) near10 (die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:51
5	277	memory near5 interfaces\$ near5 (chip or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:52
6	10	memory near interfaces\$ near (chip or die)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:55
7	814	(711/103).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 10:55
8	13	interfaces\$ near10 (memory or storage) near10 ("same" or common) adj (die or chip)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:09
9	69	(DRAM with (flash adj memory)) with (reason\$1 or advantage\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:13
10	39	(DRAM near5 (flash adj memory)) with (reason\$1 or advantage\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:14
11	32	(DRAM near5 (flash adj memory)) near10 (reason\$1 or advantage\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:19
12	2559	((volatile) or DRAM or SDRAM) near10 ((non-volatile) or (flash adj memory)) near10 (reason\$1 or advantage\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:22
13	47	(DRAM or SDRAM) near10 (flash adj memory) near10 (reason\$1 or advantage\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:23
14	18	(DRAM or SDRAM) near10 instead\$3 near10 (flash adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/30 11:24